
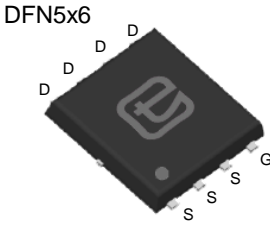
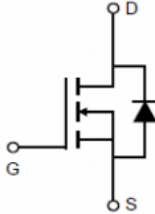


**100V N-Channel DTMOS**

Features <ul style="list-style-type: none"> ● Trench Power DTMOS Technology ● Low $R_{DS(ON)}$ ● Low Gate Charge ● Optimized for Fast-switching Applications 		Product Summary	
Applications <ul style="list-style-type: none"> ● Synchronous Rectification in DC/DC and AC/DC Converters ● Isolated DC/DC Converters in Telecom and Industrial 		V_{DS} 100V $R_{DS(ON)}$ (at $V_{GS}=10V$) < 23m Ω $R_{DS(ON)}$ (at $V_{GS}=4.5V$) < 33m Ω I_D (at $V_{GS}=10V$) 36A 100% UIS Tested	
 			
Device	Package	Marking	
TSG10N10AT	DFN5×6	10N10AT	

Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0V$)	V_{DSS}	100	V
Continuous Drain Current	I_D	$T_C = 25^\circ C$	36
		$T_C = 100^\circ C$	21.6
Pulsed Drain Current (note1)	I_{DM}	144	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	10	mJ
Avalanche Current (note1)	I_{AS}	14	A
Power Dissipation ($T_C = 25^\circ C$)	P_D	56.5	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+175	$^\circ C$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	2.1	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Value			Unit		
			Min.	Typ.	Max.			
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	--	--	V		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA		
		$V_{DS} = 100V, V_{GS} = 0V, T_J = 100^\circ\text{C}$	--	--	100			
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1	--	2.5	V		
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$	--	19	23	m Ω		
		$V_{GS} = 4.5V, I_D = 16A$	--	23	33			
Forward Transconductance (Note3)	g_{fs}	$V_{DS} = 5V, I_D = 20A$	--	40	--	S		
Dynamic								
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$ $f = 1.0MHz$	--	1134	--	pF		
Output Capacitance	C_{oss}		--	92	--			
Reverse Transfer Capacitance	C_{rss}		--	10.3	--			
Total Gate Charge	$Q_g(10V)$	$V_{DD} = 50V, I_D = 20A,$ $V_{GS} = 10V$	--	21	--	nC		
	$Q_g(4.5V)$		--	11	--			
Gate-Source Charge	Q_{gs}		--	3.1	--			
Gate-Drain Charge	Q_{gd}		--	5.1	--			
Turn-on Delay Time	$t_{d(on)}$		$V_{DD} = 50V, I_D = 20A,$ $R_G = 3\Omega$	--	7		--	ns
Turn-on Rise Time	t_r			--	3		--	
Turn-off Delay Time	$t_{d(off)}$	--		20	--			
Turn-off Fall Time	t_f	--		3	--			
Drain-Source Body Diode Characteristics								
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	37	A		
Pulsed Diode Forward Current	I_{SM}		--	--	148			
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 1A, V_{GS} = 0V$	--	0.72	1	V		
Reverse Recovery Time	t_{rr}	$I_F = 20A,$ $di_F/dt = 500A/\mu s$	--	25	--	ns		
Reverse Recovery Charge	Q_{rr}		--	120	--	nC		

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. $I_{AS} = 14A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

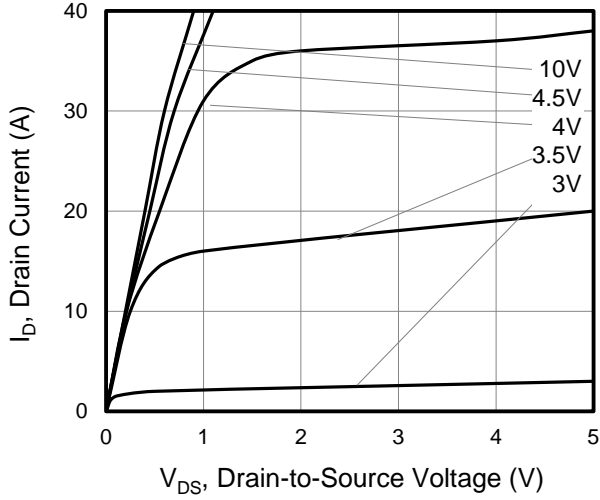


Figure 2. Transfer Characteristics

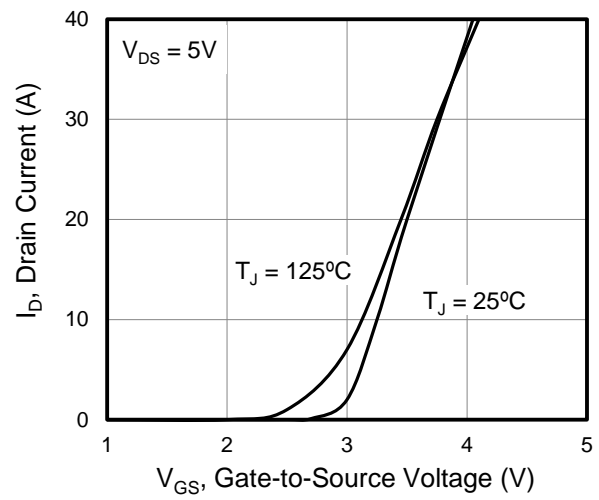


Figure 3. On-Resistance vs. Drain Current

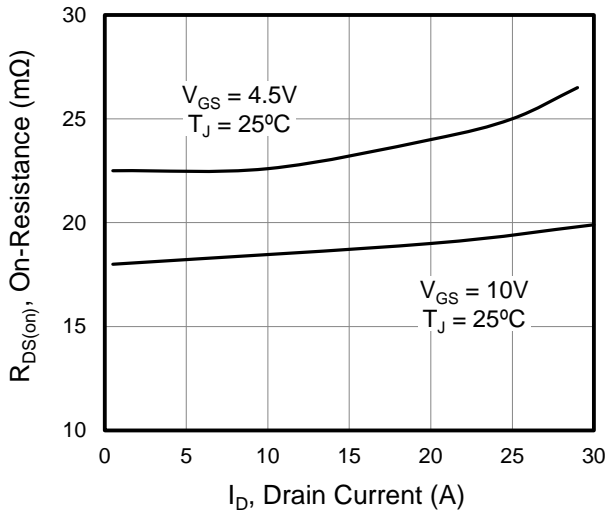


Figure 4. Capacitance

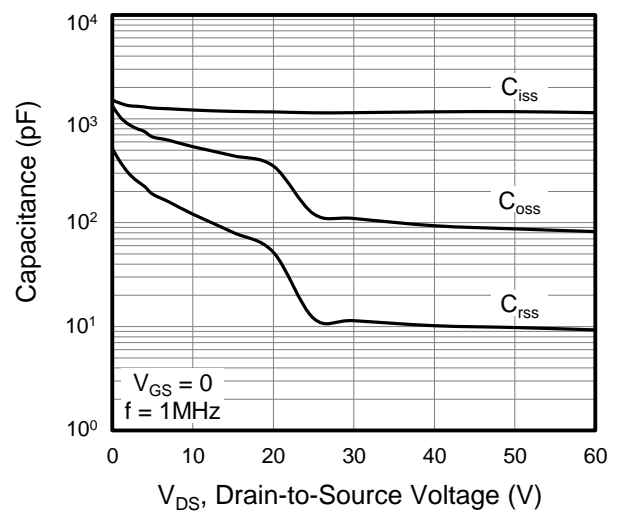


Figure 5. Gate Charge

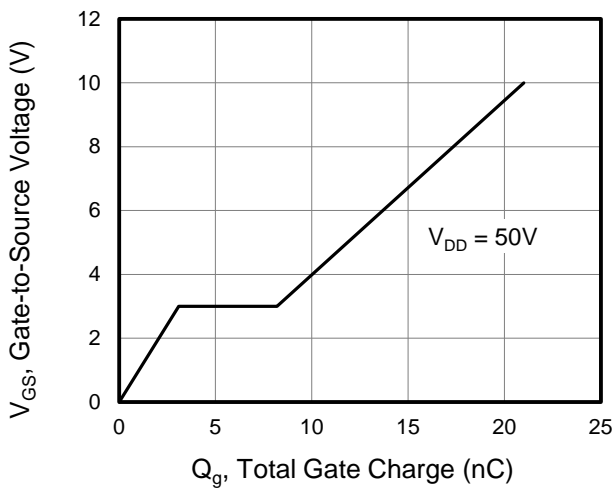
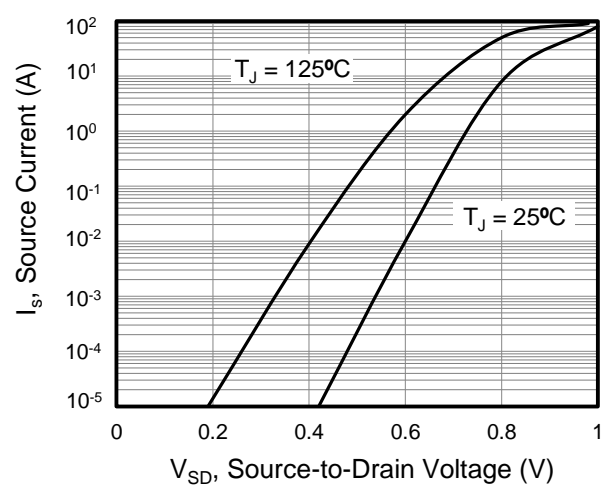


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

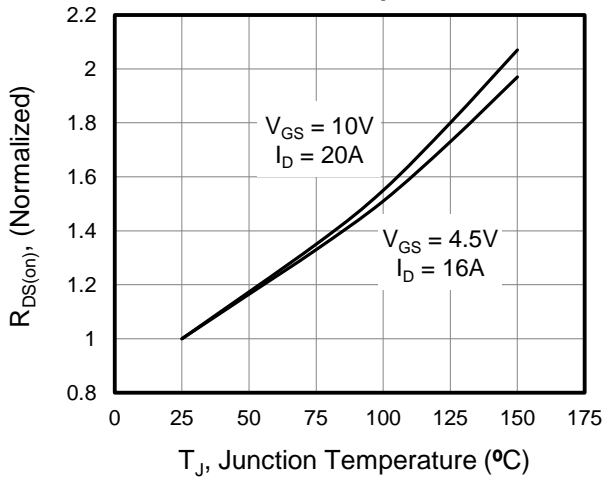


Figure 8. Threshold Voltage vs. Junction Temperature

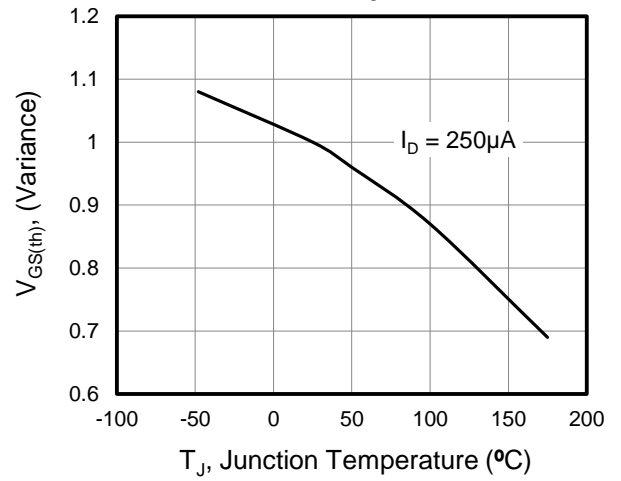


Figure 9. Transient Thermal Impedance

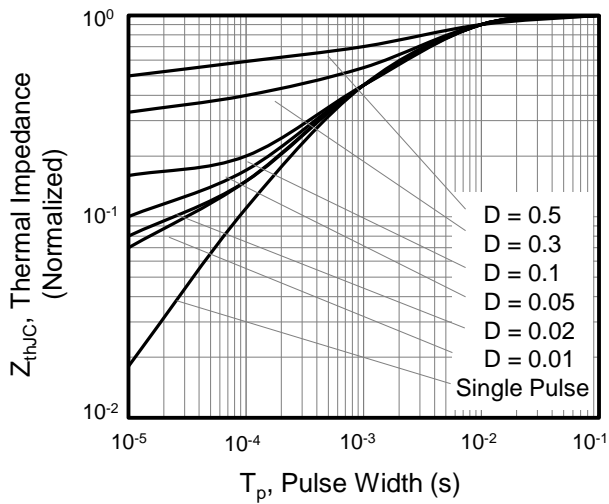


Figure 10. Safe operation area

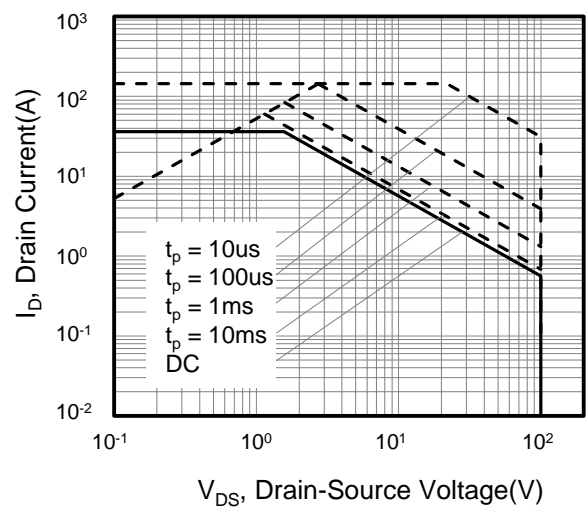




Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

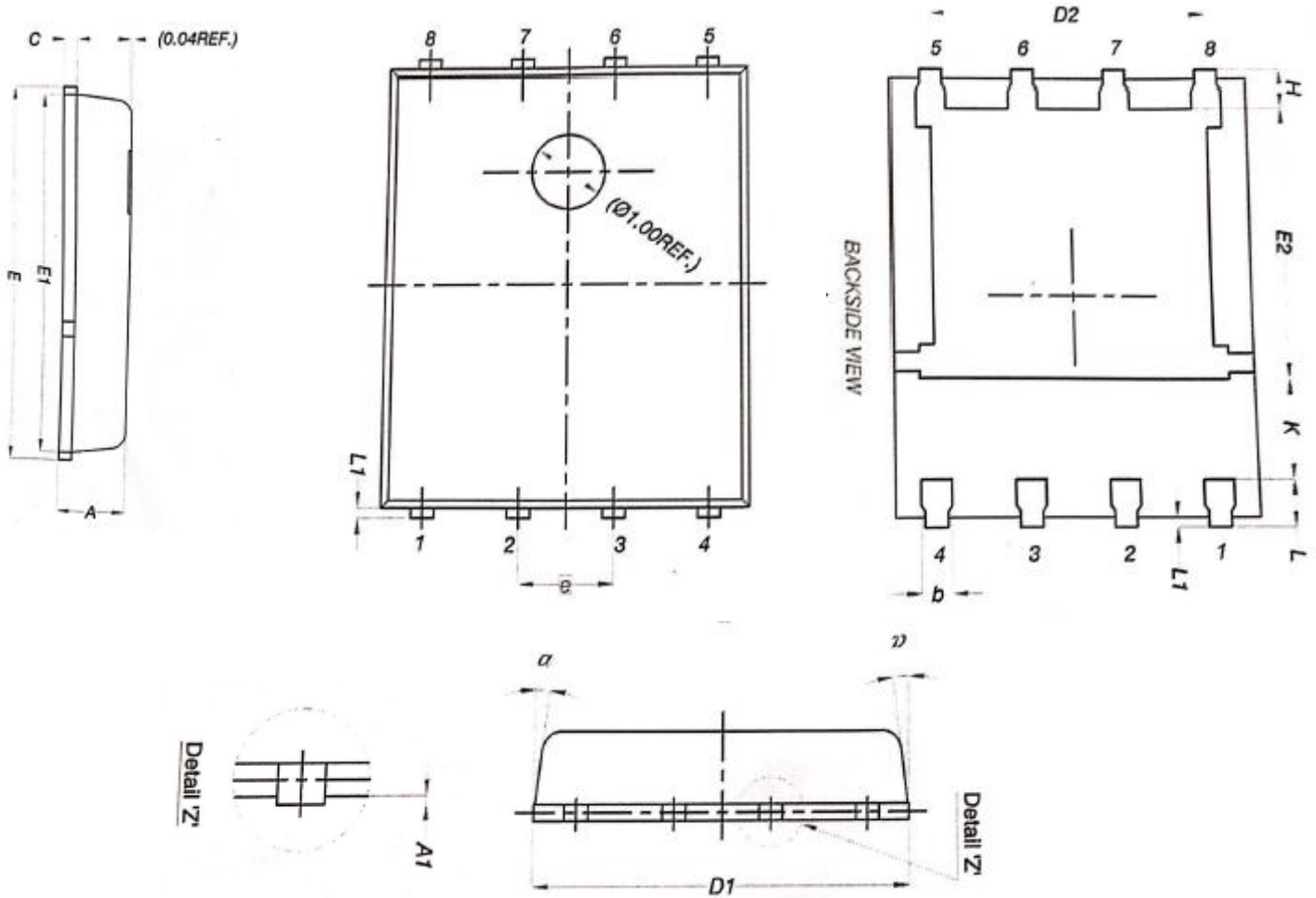


Figure C: Unclamped Inductive Switching Test Circuit and Waveform

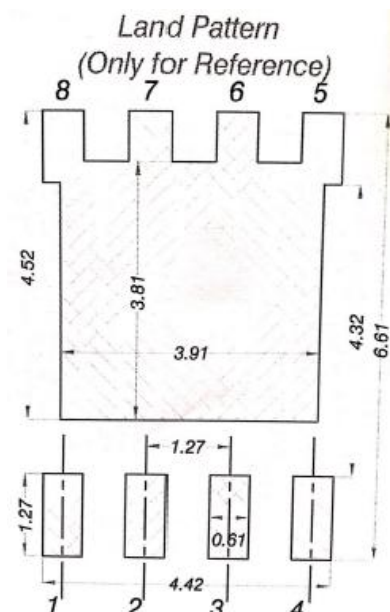




DFN5×6 PACKAGR OUTLINE



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
[e]	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°





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